Preferred Devices

Power Management, Dual Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These are Pb–Free Devices

MAXIMUM RATINGS

Rating	Symbol	Value	Unit				
\mathbf{Q}_1 (T _A = 25°C unless otherwise noted, common for Q ₁ and Q ₂)							
Collector-Base Voltage	V _{CBO}	50	Vdc				
Collector-Emitter Voltage	V _{CEO}	50	Vdc				
Collector Current	Ι _C	100	mAdc				
Electrostatic Discharge	ESD	HBM Class 1 MM Class B					
Q₂ (T _A = 25°C)		-					
Collector-Emitter Voltage	V _{CEO}	-12	Vdc				
Collector-Base Voltage	V _{CBO}	-15	Vdc				
Emitter-Base Voltage	V _{EBO}	-6.0	Vdc				
Collector Current – Peak – Continuous	Ι _C	-1.0 (Note 1) -0.5	Adc				
Electrostatic Discharge	ESD	HBM Class 3B					

IDIVI CIASS 3D
MM Class C

THERMAL CHARACTERISTICS

Characteristic				
(One Junction Heated)	Symbol	Max	Unit	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	357 (Note 2) 2.9 (Note 2)	mW mW/°C	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 2)	°C/W	
Characteristic (Both Junctions Heated)	Symbol	Max	Unit	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	500 (Note 2) 4.0 (Note 2)	mW mW/°C	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 2)	°C/W	
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

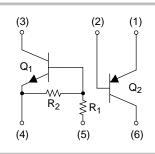
1. Single pulse 1.0 ms.

2. FR-4 @ Minimum Pad.



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SOT-563 CASE 463A PLASTIC

MARKING DIAGRAM



UY = Specific Device Code M = Date Code • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
EMF5XV6T5	SOT–563 (Pb–Free)	8000/Tape & Reel
EMF5XV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

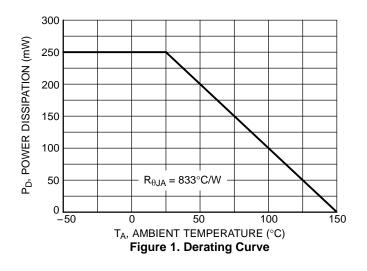
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, common for Q_1 and Q_2)

Chara	Symbol	Min	Тур	Мах	Unit	
Q ₁ OFF CHARACTERISTICS				-		
Collector-Base Cutoff Current	$(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	-	_	100	nAdc
Collector-Emitter Cutoff Current	$(V_{CE} = 50 \text{ V}, \text{ I}_{B} = 0)$	I _{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current	$(V_{EB} = 6.0 \text{ V}, \text{ I}_{C} = 0)$	I _{EBO}	-	-	0.1	mAdc
Collector-Base Breakdown Voltage	$(I_{C} = 10 \ \mu A, \ I_{E} = 0)$	V _{(BR)CBO}	50	_	-	Vdc
Collector-Emitter Breakdown Voltage (I	Note 3) $(I_{\rm C} = 2.0 \text{ mA}, I_{\rm B} = 0)$	V _{(BR)CEO}	50	-	-	Vdc
ON CHARACTERISTICS (Note 3)						
DC Current Gain	(V _{CE} = 10 V, I _C = 5.0 mA)	h _{FE}	80	140	-	
Collector-Emitter Saturation Voltage	(I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}	-	_	0.25	Vdc
Output Voltage (on)	(V _{CC} = 5.0 V, V _B = 3.5 V, R _L = 1.0 k Ω)	V _{OL}	-	_	0.2	Vdc
Output Voltage (off)	(V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 k\Omega)	V _{OH}	4.9	-	-	Vdc
Input Resistor		R1	32.9	47	61.1	kΩ
Resistor Ratio		R1/R2	0.8	1.0	1.2	
Q2 OFF CHARACTERISTICS Collector – Emitter Breakdown Voltage	(I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-12	_	-	Vdc
	$\Pi C = -\Pi U \Pi A U U \Pi B = 0$			-		
Collector_Base Breakdown Voltage				_		
Collector – Base Breakdown Voltage	$(I_{\rm C} = -0.1 \text{ mAdc}, I_{\rm E} = 0)$	V _{(BR)CBO}	-15	-	-	Vdc
Emitter – Base Breakdown Voltage	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$	V _{(BR)CBO} V _{(BR)EBO}			-	Vdc Vdc
Emitter – Base Breakdown Voltage Collector Cutoff Current	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$	V _{(BR)CBO} V _{(BR)EBO} I _{CBO}	-15 -6.0 -		- - -0.1	Vdc Vdc μAdc
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$	V _{(BR)CBO} V _{(BR)EBO}	-15	- - -	-	Vdc Vdc μAdc
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$	V _{(BR)CBO} V _{(BR)EBO} I _{CBO} I _{EBO}	-15 -6.0 -		- - -0.1	Vdc Vdc
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current ON CHARACTERISTICS	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$ $(V_{EB} = -6.0 \text{ Vdc})$ $(I_{C} = -10 \text{ mA}, V_{CE} = -2.0 \text{ V})$	V _{(BR)CBO} V _{(BR)EBO} I _{CBO} I _{EBO} h _{FE}	-15 -6.0 -		- -0.1 -0.1	Vdc Vdc μAdc
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current ON CHARACTERISTICS DC Current Gain (Note 4)	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$ $(V_{EB} = -6.0 \text{ Vdc})$ $(I_{C} = -10 \text{ mA}, V_{CE} = -2.0 \text{ V})$ Note 4) $(I_{C} = -200 \text{ mA}, I_{B} = -10 \text{ mA})$	V _{(BR)CBO} V _{(BR)EBO} I _{CBO} I _{EBO} h _{FE} V _{CE(sat)}	-15 -6.0 - - 270		- -0.1 -0.1 680	Vdc Vdc μAdc μAdc
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current ON CHARACTERISTICS DC Current Gain (Note 4) Collector – Emitter Saturation Voltage (I	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$ $(V_{EB} = -6.0 \text{ Vdc})$ $(I_{C} = -10 \text{ mA}, V_{CE} = -2.0 \text{ V})$ $(I_{C} = -200 \text{ mA}, I_{B} = -10 \text{ mA})$ $(I_{C} = -150 \text{ mA}, I_{B} = -20 \text{ mA})$	V _{(BR)CBO} V _{(BR)EBO} I _{CBO} I _{EBO} h _{FE}	-15 -6.0 - 270 -	- - -	- -0.1 -0.1 680 -250	Vdc Vdc μAdc μAdc mV
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current ON CHARACTERISTICS DC Current Gain (Note 4) Collector – Emitter Saturation Voltage (Note	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$ $(V_{EB} = -6.0 \text{ Vdc})$ $(I_{C} = -10 \text{ mA}, V_{CE} = -2.0 \text{ V})$ $(I_{C} = -200 \text{ mA}, I_{B} = -10 \text{ mA})$ $(I_{C} = -150 \text{ mA}, I_{B} = -20 \text{ mA})$	V _{(BR)CBO} V _{(BR)EBO} I _{CBO} I _{EBO} h _{FE} V _{CE(sat)} V _{BE(sat)}	-15 -6.0 - - 270 - -	- - - - - - - 0.81	- -0.1 -0.1 680 -250 -0.90	Vdc Vdc μAdc μAdc mV
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current ON CHARACTERISTICS DC Current Gain (Note 4) Collector – Emitter Saturation Voltage (Note Base – Emitter Turn–on Voltage (Note 4)	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$ $(V_{EB} = -6.0 \text{ Vdc})$ $(I_{C} = -10 \text{ mA}, V_{CE} = -2.0 \text{ V})$ $(I_{C} = -200 \text{ mA}, I_{B} = -10 \text{ mA})$ $(I_{C} = -150 \text{ mA}, I_{B} = -20 \text{ mA})$ $(I_{C} = -150 \text{ mA}, V_{CE} = -3.0 \text{ V})$	V _{(BR)CBO} V _{(BR)EBO} I _{CBO} I _{EBO} V _{CE(sat)} V _{BE(sat)}	-15 -6.0 - - 270 - - - -	- - - - - - - - 0.81 - 0.81	- -0.1 -0.1 680 -250 -0.90 -0.875	Vdc Vdc μAdc μAdc mV V
Emitter – Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current ON CHARACTERISTICS DC Current Gain (Note 4) Collector – Emitter Saturation Voltage (I Base – Emitter Saturation Voltage (Note 4) Base – Emitter Turn–on Voltage (Note 4) Input Capacitance	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$ $(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$ $(V_{CB} = -15 \text{ Vdc}, I_{E} = 0)$ $(V_{EB} = -6.0 \text{ Vdc})$ $(I_{C} = -10 \text{ mA}, V_{CE} = -2.0 \text{ V})$ $(I_{C} = -200 \text{ mA}, I_{B} = -10 \text{ mA})$ $(I_{C} = -150 \text{ mA}, I_{B} = -20 \text{ mA})$ $(I_{C} = -150 \text{ mA}, V_{CE} = -3.0 \text{ V})$ $(V_{EB} = 0 \text{ V}, f = 1.0 \text{ MHz})$	V(BR)CBO V(BR)EBO ICBO IEBO NFE VCE(sat) VBE(sat) VBE(on) Cibo	-15 -6.0 - - 270 - - - - - -	- - - - -0.81 -0.81 52	- -0.1 -0.1 680 -250 -0.90 -0.875 -	Vdc Vdc μAdc μAdc mV V V

4. Pulsed Condition: Pulse Width = $300 \ \mu$ sec, Duty Cycle $\leq 2\%$.



TYPICAL ELECTRICAL CHARACTERISTICS FOR Q1

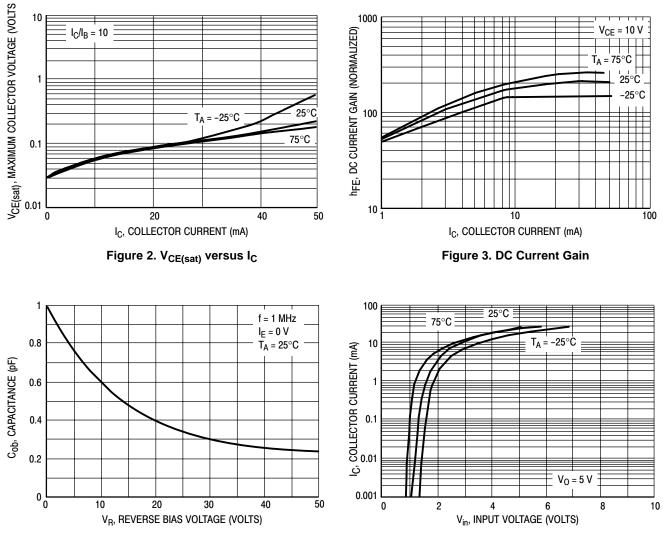


Figure 4. Output Capacitance

Figure 5. Output Current versus Input Voltage

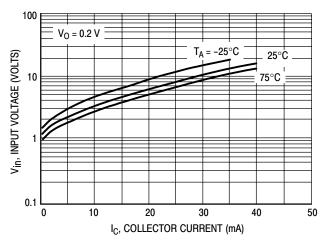
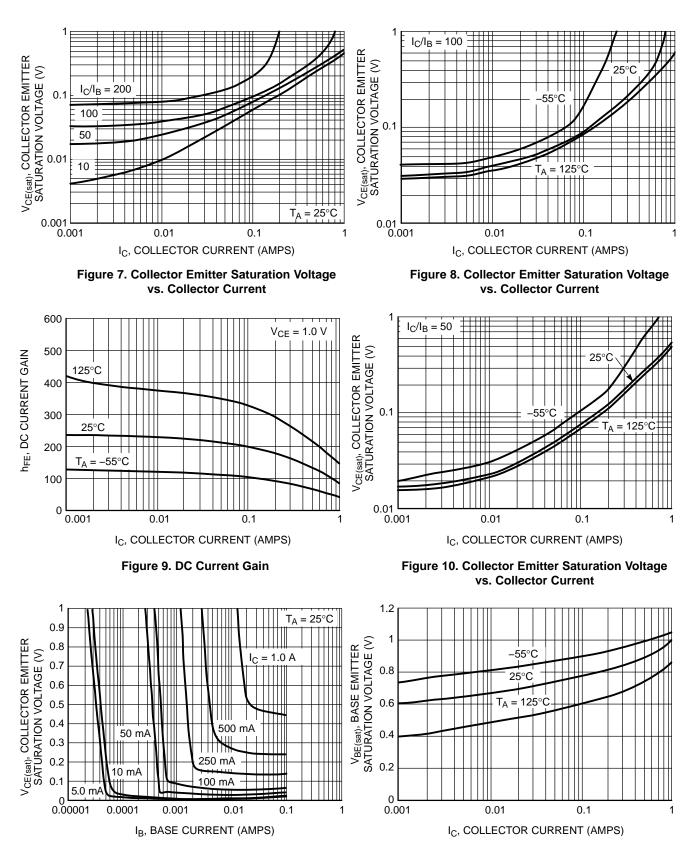


Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS FOR Q2







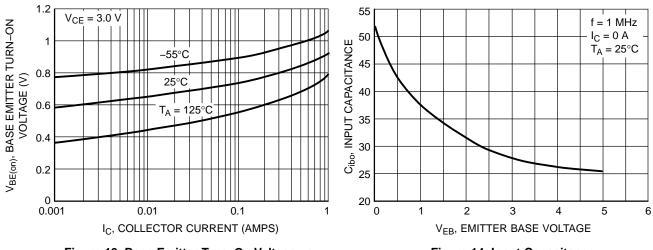


Figure 13. Base Emitter Turn–On Voltage vs. Collector Current

Figure 14. Input Capacitance

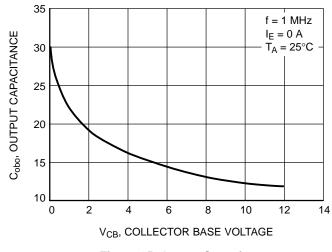
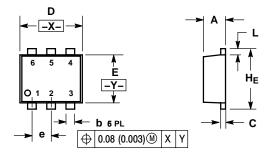


Figure 15. Output Capacitance

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01 ISSUE F



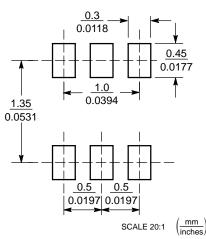
NOTES

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS

MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS 3. IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
Е	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC			0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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